RF Magnetron Sputtering of Silicon Carbide and Silicon Nitride Films for Solar Cells

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(Received 19 May 2014; published online 15 July 2014)

RF-magnetron nonreactive sputtering method from solid-phase target in argon atmosphere was used for obtaining thin silicon carbide and silicon nitride films, that are used for constructing solar cells based on substrates of single crystal silicon of p-type.

Keywords: Atomic force microscopy, RF- magnetron sputtering, Silicon carbide, Silicon nitride, Thin films, Solar cells

PACS number: 61.10.Eq

1. INTRODUCTION

Silicon carbide and silicon nitride are widely used in electronics because of their unique properties. SiC is often used for creating power electronic devices, which performance exceeds silicon-based devices. Memory effect in Si₃N₄ is used in the non-volatile devices (flash memory) [1-3]. In many cases, the widespread use of carbide and silicon nitride in heterostructures of electronic devices is associated with high permittivity of these materials (amorphous Si₃N₄ ε = 7.5 and for 4H-SiC ε = 9.6–10.0 at T = 300 K). In the case of creating a solar cell (SC) with the use of films of these materials, they are most commonly used as the upper antireflection layers in heterostructures or as passivation layers silicon surface [7]. The use of SiC has good prospects for creating pin solar cells as a wide band of light absorbing material, which heterostructures based on SiC have already achieved an efficiency SC exceeding 15 % [8,9]. Widely spread application of silicon carbide and silicon nitride in the production of solar cells and electronics in general is connected with the use of effective thin-film technology and new design solutions. Currently the most often used methods for preparation of SiC and Si₃N₄ represent different modifications of the chemical vapor deposition (CVD) method. Using comprehensive and environmentally hazardous methods of producing thin films of these materials hinders their widespread use in solar energy. For example, these technologies for the preparation of the a-SiC thin films, environmentally harmful silane (SiH₄), propane (C₃H₈) and phosphine (PH₃) are used [9, 10]. The aim of this study is to apply environmentally friendly rf- magnetron sputtering method for carbides and nitrides of silicon thin films for solar cell devices.

2. EXPERIMENTAL SECTION

Films of amorphous plus microcrystalline (α + μc) SiC and Si₃N₄ were obtained by nonreactive magnetron sputtering, using solid state target on plant VN-2000. The depositions were carried out on a cold and hot substrates of p-Si (100) with a resistivity of 2 Ohm-cm. Before layering the layer of native oxide SiO₂ was extracted from the substrate by etching in HF. Thicknesses of the films were controlled by atomic-force microscopy methods (AFM) according to heigh of steps on the edge of the film. The compositions of deposited films were characterized by Raman Spectroscopy (RS) techniques using co-focal nanometric resolution Omega Scope AIST-N. Raman microscope with Ar⁺ laser excitation at 532 nm. The morphology features of the thin layers were studied by tapping-mode AFM (NTEGRA Aura, NT-MDT) in a controlled atmosphere or low vacuum. The amorphous plus microcrystalline nature of the films is confirmed by the results of electron diffraction obtained on SiC and Si₃N₄ specially prepared samples in a JEOL Ltd. JEM 2100 transmission electron microscope.

3. RESULTS AND DISCUSSION

For characterization of SiC nanolayers the Raman Spectroscopy (RS) techniques were used. The Raman spectrum show a dominant band at 982 cm⁻¹, i.e. in the spectral region close to the frequency of the modes characteristic of SiC [11]. The morphology features of SiC thin films were studied by AFM. The average height of the surface features varies when the film thickness 1-2 nm, 3-5 nm and 25-35 nm when the film thickness changes from 2 nm to 6 nm and 56 nm, respectively. The lateral dimensions of those elements are of the order of tens of nanometres. A 2D autocorrelation function was applied to the AFM images. It was found that Sa, average roughness increases along growth the film thickness and equals to 0.2, 0.9 and 7.3 nm for the film thickness 1-2 nm, 3-5 nm and 25-35 nm, respectively. Mixed of cubic symmetry microcrystalline plus amorphous nature of the films is confirmed by the results of electron diffraction obtained on SiC films in a JEOL Ltd. JEM 2100 transmission electron microscope.

Were performed AFM studies and a comparative analysis of thin films Si₃N₄ grown by rf-magnetron sputtering on a cold (T_s = 40 °C) and hot (T_s = 800 °C) substrate. The results of these studies are shown in Figure 3. As a result of analysis the AFM images, it was established that the increment of the relative magnitude of the surface area (Sa) increased from 0.8 % for Ts = 40 °C, up to – 8.9 % for Ts = 800 °C.
The compositions of Si$_3$N$_4$ films were characterized by RS techniques. The position of the maximum in the spectrum of Raman scattering corresponds to the compound Si$_3$N$_4$, and the shape of the spectrum is characteristic of the nano crystalline state.

Peak-to-peak  9.146 nm  
Root mean square, RMS  1.311 nm  
Roughness average  1.046 nm  
Skewness, Ssk  0.789  
Kurtosis, Ska  3.463  
Sdr, Surface area ratio  0.806 %
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Peak-to-peak 36.307 nm
Root mean square, RMS 5.136 nm
Roughness average 3.958 nm
Skewness, Ssk 0.955
Kurtosis, Ska 3.947
Sdr, Surface area ratio 8.966 %

Fig.3. – AFM images of free surfaces Si3N4 films for rf-sputtering substrate temperatures (a) \( Ts = 40 \) °C, (b) \( Ts = 800 \) °C and results of calculations S-parameters (a surface area) or 3D-parameters, characterizing the structure in three dimensions

4. CONCLUSIONS

Thus using our method of nonreactive rf-magnetron sputtering were obtained nanoscale and nanostructured homogeneous films \((a + \mu\epsilon)\) SiC and Si3N4. Were studied their surface morphology, structure and composition. The possibility of increasing more than 10 times the relative surface area Sdr, which is an important indicator for the light-absorbing layers SC.

This study was supported by the Ministry of Education and Science of the Russian Federation: reference number 2014/420-367.

REFERENCES